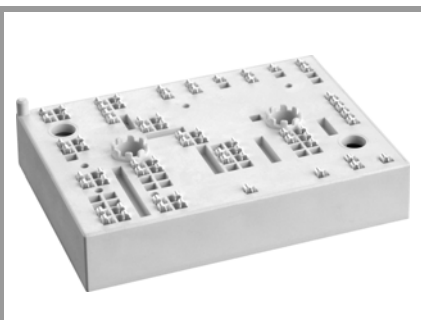


# SKiiP 35ACC12T4V10



MiniSKiiP® 3

## Twin 6-pack

### SKiiP 35ACC12T4V10

#### Target Data

#### Features

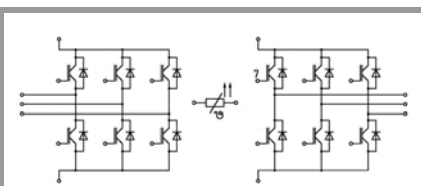
- Trench 4 IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532

#### Typical Applications\*

- 4Q inverters
- Double axis inverters

#### Remarks

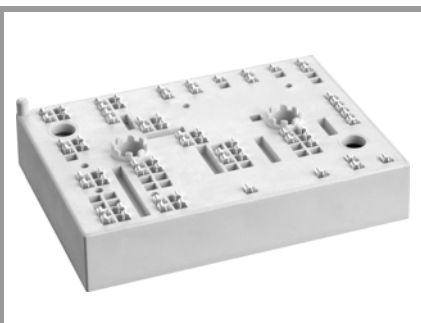
- Max. case temperature limited to  $T_C = 125^\circ\text{C}$
- Product reliability results valid for  $T_j \leq 150^\circ\text{C}$  (recommended  $T_{j,op} = -40 \dots +150^\circ\text{C}$ )



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Absolute Maximum Ratings				
Symbol	Conditions	Values	Unit	
<b>IGBT 1 - 6</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	1200	V	
$I_C$	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	62	A
		$T_s = 70^\circ\text{C}$	47	A
$I_C$	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	69	A
		$T_s = 70^\circ\text{C}$	56	A
$I_{Cnom}$		50	A	
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$	150	A	
$V_{GES}$		-20 ... 20	V	
$t_{psc}$	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 150^\circ\text{C}$	10	$\mu\text{s}$
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>IGBT 7 - 12</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	1200	V	
$I_C$	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	62	A
		$T_s = 70^\circ\text{C}$	47	A
$I_C$	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	69	A
		$T_s = 70^\circ\text{C}$	56	A
$I_{Cnom}$		50	A	
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$	150	A	
$V_{GES}$		-20 ... 20	V	
$t_{psc}$	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 150^\circ\text{C}$	10	$\mu\text{s}$
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Diode 1 - 6</b>				
$V_{RRM}$	$T_j = 25^\circ\text{C}$	1200	V	
$I_F$	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	52	A
		$T_s = 70^\circ\text{C}$	39	A
$I_F$	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	60	A
		$T_s = 70^\circ\text{C}$	48	A
$I_{Fnom}$		50	A	
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$	150	A	
$I_{FSM}$	10 ms, sin 180°, $T_j = 150^\circ\text{C}$	270	A	
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Diode 7 - 12</b>				
$V_{RRM}$	$T_j = 25^\circ\text{C}$	1200	V	
$I_F$	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	54	A
		$T_s = 70^\circ\text{C}$	41	A
$I_F$	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	60	A
		$T_s = 70^\circ\text{C}$	48	A
$I_{Fnom}$		50	A	
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$	150	A	
$I_{FSM}$	10 ms, sin 180°, $T_j = 150^\circ\text{C}$	270	A	
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Module</b>				
$I_{t(RMS)}$	20 A per spring	60	A	
$T_{stg}$		-40 ... 125	$^\circ\text{C}$	
$V_{isol}$	AC sinus 50 Hz, 1 min	2500	V	

# SKiiP 35ACC12T4V10



MiniSKiiP® 3

## Twin 6-pack

### SKiiP 35ACC12T4V10

#### Target Data

#### Features

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- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532

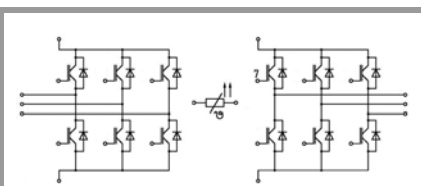
#### Typical Applications\*

- 4Q inverters
- Double axis inverters

#### Remarks

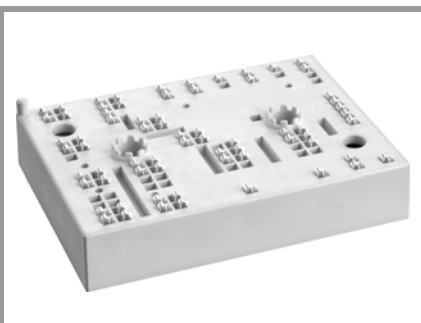
- Max. case temperature limited to  $T_C = 125^\circ\text{C}$
- Product reliability results valid for  $T_j \leq 150^\circ\text{C}$  (recommended)  
 $T_{j,op} = -40 \dots +150^\circ\text{C}$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>IGBT 1 - 6</b>						
$V_{CE(sat)}$	$I_C = 50\text{ A}$ $V_{GE} = 15\text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$		1.85	2.10	V
		$T_j = 150^\circ\text{C}$		2.25	2.40	V
$V_{CE0}$	chipllevel	$T_j = 25^\circ\text{C}$		0.8	0.9	V
		$T_j = 150^\circ\text{C}$		0.7	0.8	V
$r_{CE}$	$V_{GE} = 15\text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$		21	24	m $\Omega$
		$T_j = 150^\circ\text{C}$		31	32	m $\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}\text{ V}, I_C = 1.7\text{ mA}$		5	5.8	6.5	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$		0.1	0.3	mA
						mA
$C_{ies}$	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$		2.77		nF
$C_{oes}$		$f = 1\text{ MHz}$		0.21		nF
$C_{res}$		$f = 1\text{ MHz}$		0.16		nF
$Q_G$	$V_{GE} = -8\text{ V} \dots +15\text{ V}$			280		nC
$R_{Gint}$	$T_j = 25^\circ\text{C}$			4		$\Omega$
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$				ns
$t_r$	$I_C = 50\text{ A}$	$T_j = 150^\circ\text{C}$				ns
$E_{on}$		$T_j = 150^\circ\text{C}$				mJ
$t_{d(off)}$		$T_j = 150^\circ\text{C}$				ns
$t_f$		$T_j = 150^\circ\text{C}$				ns
$E_{off}$	$V_{GE} = +15/-15\text{ V}$	$T_j = 150^\circ\text{C}$				mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste} = 0.8\text{ W/K}^*\text{m}$			0.71		K/W
<b>IGBT 7 - 12</b>						
$V_{CE(sat)}$	$I_C = 50\text{ A}$ $V_{GE} = 15\text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$		1.85	2.10	V
		$T_j = 150^\circ\text{C}$		2.20	2.40	V
$V_{CE0}$	chipllevel	$T_j = 25^\circ\text{C}$		0.80	0.90	V
		$T_j = 150^\circ\text{C}$		0.70	0.80	V
$r_{CE}$	$V_{GE} = 15\text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$		21	24	m $\Omega$
		$T_j = 150^\circ\text{C}$		30	32	m $\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}\text{ V}, I_C = 1.7\text{ mA}$		5	5.8	6.5	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$				mA
						mA
$C_{ies}$	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$		2.77		nF
$C_{oes}$		$f = 1\text{ MHz}$		0.21		nF
$C_{res}$		$f = 1\text{ MHz}$		0.16		nF
$Q_G$	$V_{GE} = -8\text{ V} \dots +15\text{ V}$			280		nC
$R_{Gint}$	$T_j = 25^\circ\text{C}$			4		$\Omega$
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$				ns
$t_r$	$I_C = 50\text{ A}$	$T_j = 150^\circ\text{C}$				ns
$E_{on}$		$T_j = 150^\circ\text{C}$				mJ
$t_{d(off)}$		$T_j = 150^\circ\text{C}$				ns
$t_f$		$T_j = 150^\circ\text{C}$				ns
$E_{off}$	$V_{GE} = +15/-15\text{ V}$	$T_j = 150^\circ\text{C}$				mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste} = 0.8\text{ W/K}^*\text{m}$			0.71		K/W



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# SKiiP 35ACC12T4V10



MiniSKiiP® 3

## Twin 6-pack

### SKiiP 35ACC12T4V10

#### Target Data

#### Features

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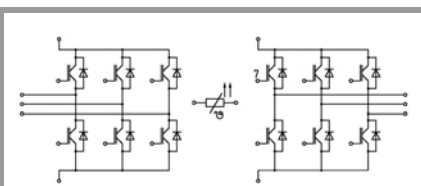
#### Typical Applications\*

- 4Q inverters
- Double axis inverters

#### Remarks

- Max. case temperature limited to  $T_C = 125^\circ\text{C}$
- Product reliability results valid for  $T_j \leq 150^\circ\text{C}$  (recommended  $T_{j,op} = -40 \dots +150^\circ\text{C}$ )

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Diode 1 - 6</b>						
$V_F = V_{EC}$	$I_F = 50\text{ A}$ $V_{GE} = 0\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$		2.2	2.7	V
		$T_j = 150^\circ\text{C}$		2.2	2.5	V
$V_{F0}$	chipelevel	$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
$r_F$	chipelevel	$T_j = 25^\circ\text{C}$		18	25	m $\Omega$
		$T_j = 150^\circ\text{C}$		26	28	m $\Omega$
$I_{RRM}$	$I_F = 50\text{ A}$	$T_j = 150^\circ\text{C}$				A
$Q_{rr}$	$V_{GE} = -15\text{ V}$ $V_R = 600\text{ V}$	$T_j = 150^\circ\text{C}$				$\mu\text{C}$
$E_{rr}$		$T_j = 150^\circ\text{C}$				mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste} = 0.8\text{ W/K}\cdot\text{m}$			0.95		K/W
<b>Diode 7 - 12</b>						
$V_F = V_{EC}$	$I_F = 50\text{ A}$ $V_{GE} = 0\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$		2.2	2.5	V
		$T_j = 150^\circ\text{C}$		2.2	2.5	V
$V_{F0}$	chipelevel	$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
$r_F$	chipelevel	$T_j = 25^\circ\text{C}$		18	21	m $\Omega$
		$T_j = 150^\circ\text{C}$		26	28	m $\Omega$
$I_{RRM}$	$I_F = 50\text{ A}$	$T_j = 150^\circ\text{C}$				A
$Q_{rr}$	$V_{GE} = -15\text{ V}$ $V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$				$\mu\text{C}$
$E_{rr}$		$T_j = 150^\circ\text{C}$				mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste} = 0.8\text{ W/K}\cdot\text{m}$			0.95		K/W
<b>Module</b>						
$M_s$	to heat sink			2	2.5	Nm
$W$				82		g
<b>Temperature Sensor</b>						
$R_{100}$	$T_r = 100^\circ\text{C}$ ( $R_{25} = 1000\Omega$ )			1670 $\pm$ 3%		$\Omega$
$R(T)$	$R(T) = 1000\Omega [1 + A(T - 25^\circ\text{C}) + B(T - 25^\circ\text{C})^2]$ ], $A = 7.635 \cdot 10^{-3} \text{ }^\circ\text{C}^{-1}$ , $B = 1.731 \cdot 10^{-5} \text{ }^\circ\text{C}^{-2}$					



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